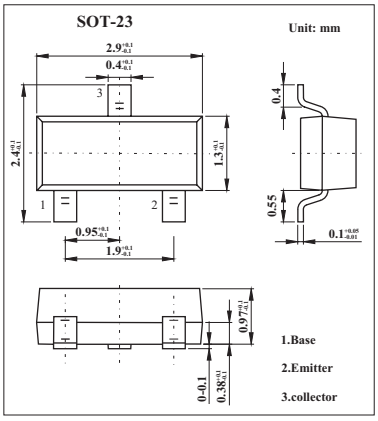
Power High Performance Transistor

FMMT495



■ Features

- SOT23 NPN silicon planar medium

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	170	V
Collector-emitter voltage	V_{CEO}	150	V
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CM}	2	A
Collector current	I_C	1	A
Base current	I_B	200	mA
Power dissipation	P_{tot}	500	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA	170			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	I_C=10mA	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA	5			V
Collector Cut-Off Currents	I_{CBO}	V_{CB}=150V			100	nA
Collector Cut-Off Currents	I_{CES}	V_{CE}=150V			100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=4V			100	nA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=250mA,I_B=25mA I_C=500mA,I_B=50mA			0.2 0.3	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C=500mA,I_B=50mA			1.0	V
Base-emitter voltage *	$V_{BE(ON)}$	I_C=500mA,V_{CE}=10V			1.0	V
Static Forward Current Transfer Ratio	h_{FE}	I_C=1mA, V_{CE}=10V	100			
		I_C=250mA, V_{CE}=10V*	100		300	
		I_C=500mA, V_{CE}=10V*	50			
		I_C=1A, V_{CE}=10V*	10			
Transition Frequency	f_T	I_C=50mA,V_{CE}=10V,f=100MHz	100			MHz
Collector-Base Breakdown Voltage	C_{obo}	V_{CB}=10V,f=1MHz			10	pF

* Pulse test: tp = 300 μs; d ⩽ 0.02.

■ Marking

Marking	495